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Width, µm	0.375	0.5	1.0
Spacing, µm	0.25	0.5	1.0
Height, µm (1.8 aspect ratio)	0.675	0.9	1.8
Resistance (Al), Ω/mm	130	73	18
Resistance (Cu), Q/mm	108	57	13
Capacitance, fF/mm (er=3.9)	296	230	230
% of Cap is Xcap	78%	69%	69%
Wire delay (Al), FO4/mm <sup>2</sup>	0.21	0.09	0.02
Wire delay (Cu), FO4/mm <sup>2</sup>	0.18	0.07	0.01

















L <sub>drawn</sub>	0.25µm	<b>0.18μm</b>	0.13μm	<b>0.10μm</b>	0.07μm	0.05μm
Mid-layer width (4 $\lambda$ ) in m $\mu$	0.50	0.36	0.26	0.20	0.14	0.10
Global layer width (8 $\lambda$ ) in $\mu$ m	1.0	0.72	0.52	0.40	0.28	0.20
Chip edge length, mm	17.3	19	20.7	22.8	24.9	27.4
FO4 delay, pS	90	65	48	36	25	18
Frequency at 16 FO4s, GHz	0.7	1	1.3	1.7	2.5	3.5

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TABLE 1. Conservative s	caling					
L <sub>drawn</sub>	0.25μm	0.18μm	0.13μm	<b>0.10μm</b>	0.07μm	0.05μn
Mid-layer R, Ω/µm	0.07	0.11	0.19	0.32	0.65	1.29
Global layer R, Ω/μm	0.018	0.026	0.044	0.074	0.15	0.30
Mid/Global C, fF/µm	0.23	0.22	0.22	0.20	0.19	0.17
TABLE 2. SIA roadmap	scaling	0.18um	0.13um	0.10um	0.07µm	0.05un
Mid-laver R. Ω/um	0.07	0.11	0.18	0.26	0.39	0.70
Global layer R, Ω/μm	0.018	0.025	0.042	0.061	0.091	0.16
Mid/Global C, fF/µm	0.23	0.19	0.18	0.16	0.16	0.16
		50	urce: Horo	witz "Futu	re of Wires'	•

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TABLE 3 Delays under scaling						
L <sub>drawn</sub>	0.25μm	0.18µm	0.13μm	0.10µm	0.07μm	0.05μm
50K block semi-perim length, mm	3580	2500	1750	1315	990	740
Conservative 50K block delay, FO4	1.2	1.2	1.4	1.5	2.3	3.4
SIA 50K block delay, FO4	0.94	1.02	1.06	1.03	1.21	1.76
Chip edge, cm	17.3	19	20.7	22.8	24.9	27.4
Conservative chip edge delay, FO4	7.0	15.3	43.7	107	345	1073
SIA chip edge delay, FO4	5.1	13	34	72	180	560
		sour	ce: Horowi	tz "Future	of Wires"	



































